

150 V, 500 mA NPN high-voltage low VCEsat (BISS) transistor
19 November 2015 Product data sheet

1. General description

NPN high-voltage low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a leadless ultra small DFN1010D-3 (SOT1215) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

PNP complement: PBHV9515QA.

2. Features and benefits

- High voltage
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FF}) at high I_C
- Low package height of 0.37 mm
- AEC-Q101 qualified
- Suitable for Automatic Optical Inspection (AOI) of solder joint

3. Applications

- LED driver for LED chain module
- High Intensity Discharge (HID) front lighting
- Automotive motor management
- Switch Mode Power Supply (SMPS)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	150	V
I _C	collector current		-	-	500	mA
h _{FE}	DC current gain	V_{CE} = 10 V; I_{C} = 100 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	100	215	-	



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	E	emitter		В
3	С	collector	4 3	- 1
4	С	collector	2	E sym123
			Transparent top view DFN1010D-3 (SOT1215)	

6. Ordering information

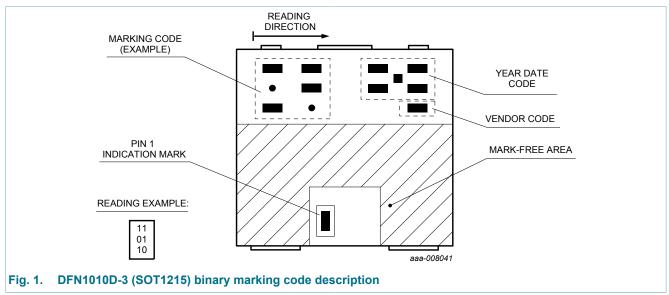
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBHV8515QA	DFN1010D-3	DFN1010D-3: plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 1.1 x 1.0 x 0.37 mm	SOT1215		

7. Marking

Table 4. Marking codes

Type number	Marking code
PBHV8515QA	00 00 11



PBHV8515QA

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	150	V
V _{CEO}	collector-emitter voltage	open base		-	150	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	500	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	1	Α
I _{BM}	peak base current			-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	325	mW
			[2]	-	600	mW
			[3]	-	740	mW
			[4]	-	540	mW
			<u>[5]</u>	-	1	W
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

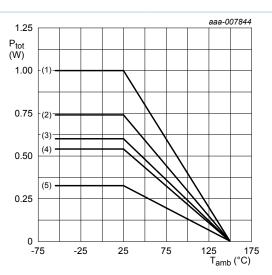
^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

^[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

^[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².



- (1) FR4 PCB, 4-layer copper, 1 cm²
- (2) FR4 PCB, single-sided copper, 6 cm²
- (3) FR4 PCB, single-sided copper, 1 cm²
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided copper, standard footprint

Fig. 2. Power derating curves

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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)} thermal resistance from junction to ambient	thermal resistance		[1]	-	-	385	K/W
			[2]	-	-	209	K/W
	ambient		<u>[3]</u>	-	-	169	K/W
			[4]	-	-	232	K/W
			<u>[5]</u>	-	-	125	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².

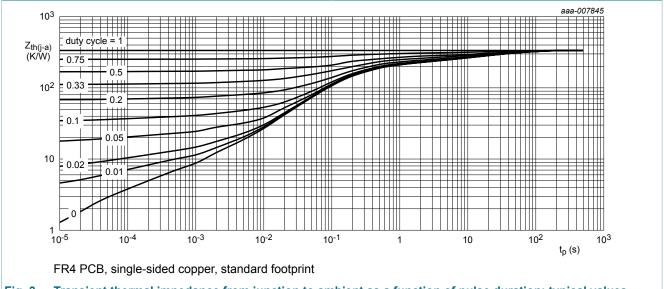


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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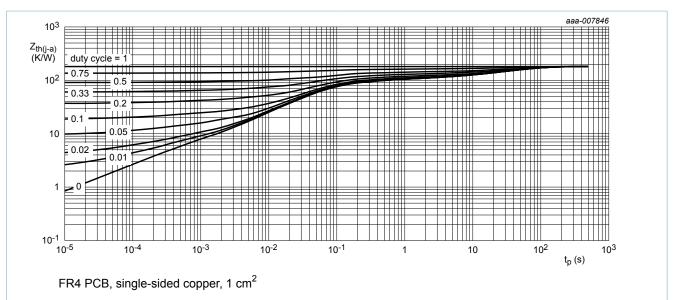


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

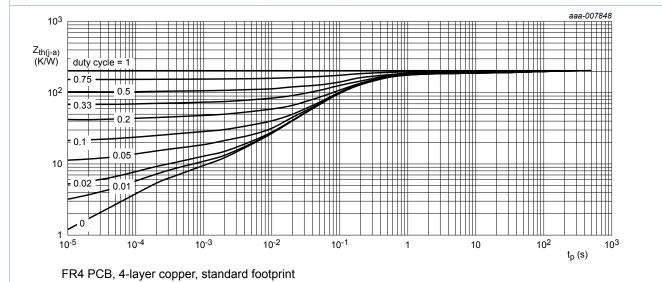
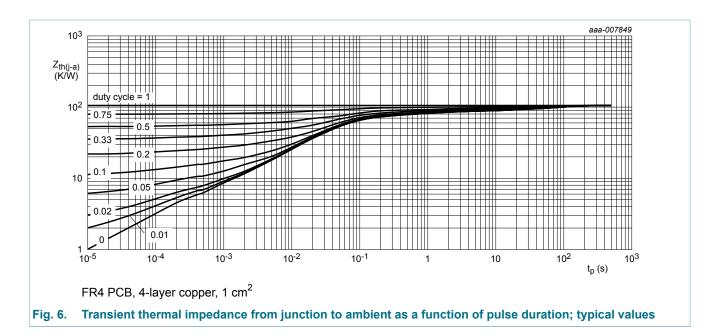


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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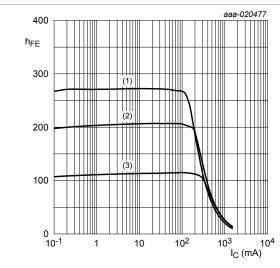
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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Ісво	collector-base cut-off	V _{CB} = 120 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 120 V; I _E = 0 A; T _j = 150 °C	-	-	10	μA
CES	collector-emitter cut-off current	V _{CE} = 120 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
EBO	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE} DC current gain	DC current gain	V_{CE} = 10 V; I_{C} = 50 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	100	215	-	
		V_{CE} = 10 V; I_{C} = 100 mA; pulsed; $t_{p} \le$ 300 µs; $\delta \le$ 0.02; T_{amb} = 25 °C	100	215	-	
		V_{CE} = 10 V; I_{C} = 200 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	100	200	-	
		V_{CE} = 10 V; I_{C} = 500 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	35	60	-	
V _{CEsat} collector-emitter saturation voltage	collector-emitter	I_C = 50 mA; I_B = 5 mA; T_{amb} = 25 °C	-	30	60	mV
	saturation voltage	I_{C} = 100 mA; I_{B} = 10 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	45	80	mV
		I_{C} = 100 mA; I_{B} = 20 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	35	70	mV
		I_{C} = 200 mA; I_{B} = 40 mA; pulsed; $t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb}$ = 25 °C	-	60	100	mV
		I_C = 500 mA; I_B = 100 mA; pulsed;	-	120	200	mV
/ _{BEsat}	base-emitter saturation voltage	$t_p \le 300 \text{ μs; } δ \le 0.02; T_{amb} = 25 \text{ °C}$	-	0.95	1.2	V
d	delay time	V _{CC} = 10 V; I _C = 100 mA; I _{Bon} = 20 mA;	-	15	-	ns
r	rise time	I _{Boff} = -20 mA; T _{amb} = 25 °C	-	155	-	ns
on	turn-on time		-	170	-	ns
s	storage time		-	650	-	ns
f	fall time		-	170	-	ns
off	turn-off time		-	820	-	ns
T	transition frequency	V _{CE} = 10 V; I _C = 10 mA; f = 100 MHz; T _{amb} = 25 °C	-	75	-	MHz
C _c	collector capacitance	$V_{CB} = 20 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$	-	2.4	-	pF

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C _e	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_C = 0 \text{ A}; i_c = 0 \text{ A};$	-	125	-	pF
		f = 1 MHz; T _{amb} = 25 °C				



 V_{CE} = 10 V

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 7. DC current gain as a function of collector current; typical values

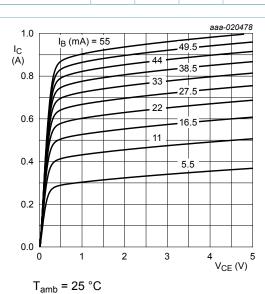
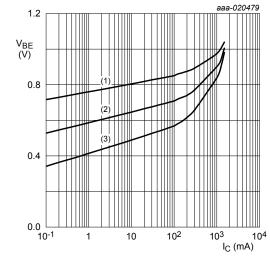


Fig. 8. Collector current as a function of collectoremitter voltage; typical values



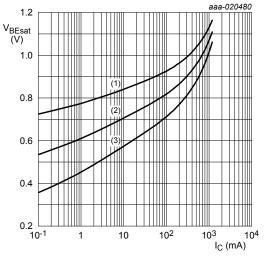
V_{CE} = 10 V

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
 = 100 °C

Fig. 9. Base-emitter voltage as a function of collector current; typical values



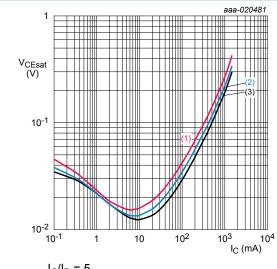
$$I_C/I_B = 5$$

(1)
$$T_{amb} = -55$$
 °C

(2)
$$T_{amb}$$
 = 25 °C

(3)
$$T_{amb}$$
= 100 °C

Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values



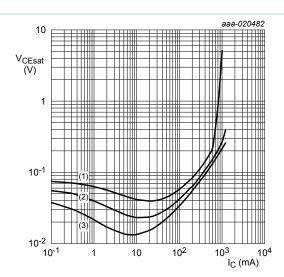
$$I_C/I_B = 5$$

(1)
$$T_{amb}$$
 = 100 °C

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 11. Collector-emitter saturation voltage as a function of collector current; typical values



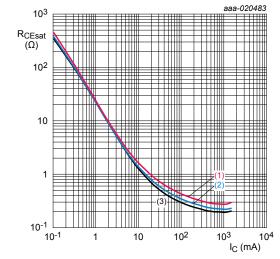
$$T_{amb}$$
 = 25 °C

(1)
$$I_C/I_B = 20$$

(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig. 12. Collector-emitter saturation voltage as a function of collector current; typical values



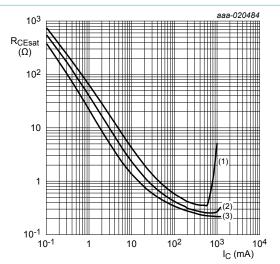
$$I_C/I_B = 5$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb}$$
 = 25 °C

$$(3) T_{amb} = -55 °C$$

Fig. 13. Collector-emitter saturation resistance as a function of collector current; typical values



$$T_{amb} = 25 \, ^{\circ}C$$

(1)
$$I_C/I_B = 20$$

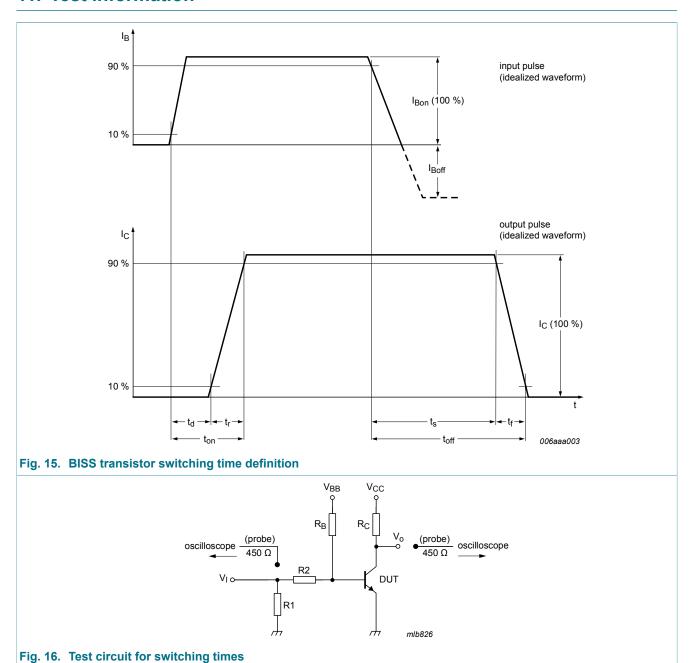
(2)
$$I_C/I_B = 10$$

(3)
$$I_C/I_B = 5$$

Fig. 14. Collector-emitter saturation resistance as a function of collector current; typical values

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11. Test information

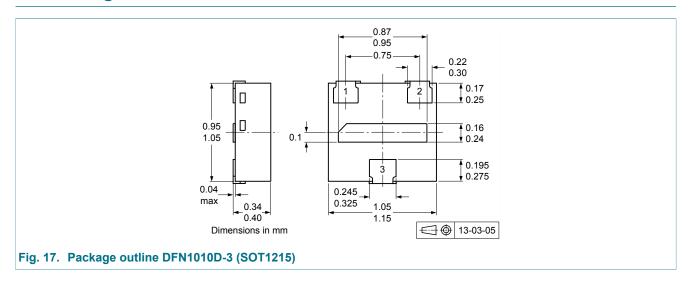


11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

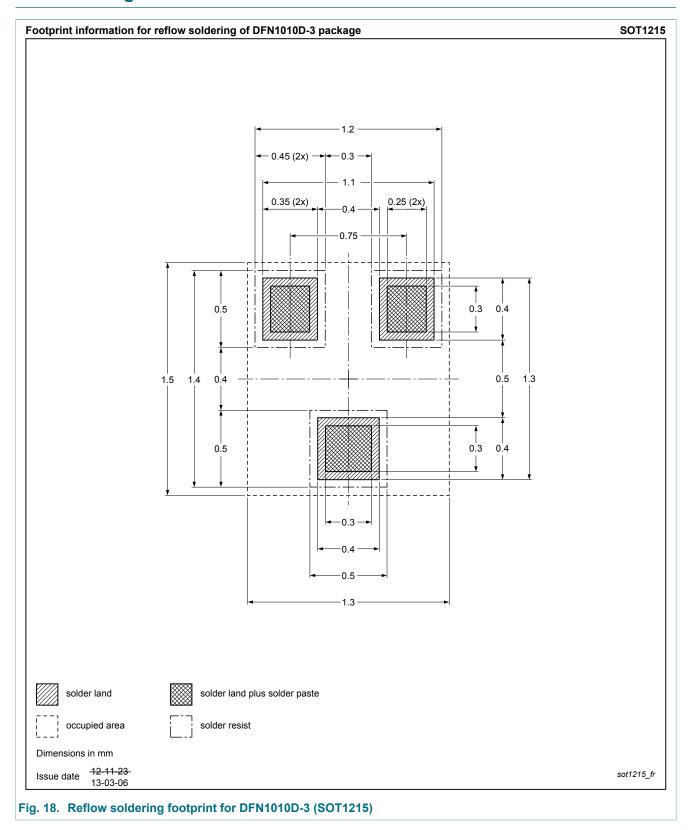
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12. Package outline



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13. Soldering



PBHV8515QA

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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBHV8515QA v.1	20151119	Product data sheet	-	-

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15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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